

SpO₂-6691

Infrared and Red Emitting Diodes

The SpO₂-6691 is a High-Power AlGaAs IRED & AlGaP/Si RED LED mounted in a clear plastic package. It is compact and easy to mount.

Features

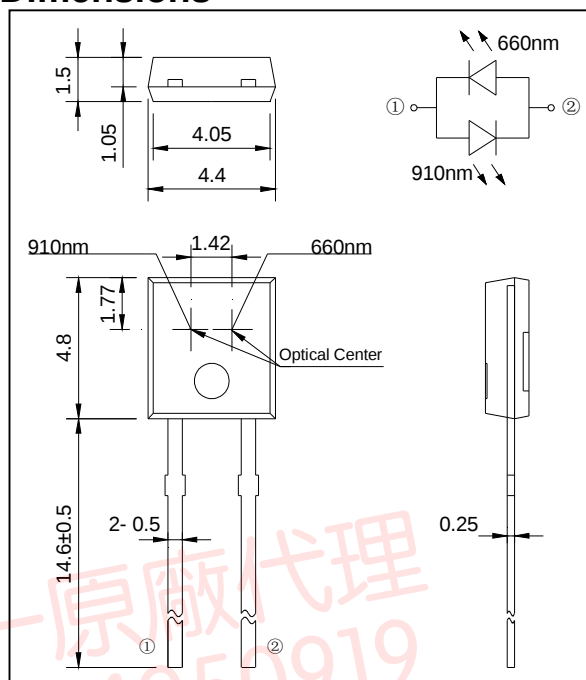
- High output
- High reliability
- Compact

Application

- SpO₂ Module
- Optical Dual Wavelength Emitter

Dimensions

(Unit:mm)



MAXIMUM RATINGS

(Ta= 25°C)

Item	Symbol	Rating		Unit
		Red	Infrared	
Power dissipation	P _D	75	100	mW
Forward current	I _F	50	50	mA
Reverse voltage	V _R	5	5	V
Operating temp.	T _{opr.}	-25~+85		°C
Storage temp.	T _{stg.}	-30~+100		°C
Soldering temp. ^{*1}	T _{sol.}	260		°C

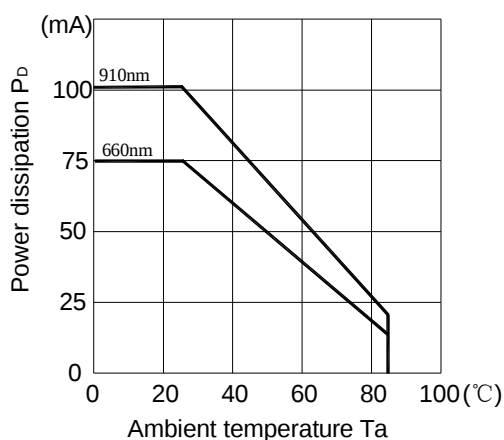
*1. Lead Soldering Temperature(3mm from case for 5sec)

ELECTRO- OPTICAL CHARACTERISTICS

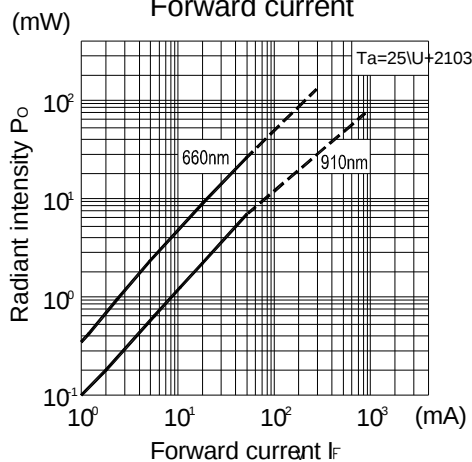
(Ta= 25°C)

Items	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =50mA	910nm	-	1.4	V
			660nm	-	2.4	V
Reverse voltage	I _R	V _R =5V	910nm	-	10	μA
			660nm	-	1	μA
Radiant intensity	I _E	I _F =50mA	910nm	-	0.6	mW/Ster
			660nm	-	5	mW/Ster
Peak wavelength	λ _p	I _F =20mA	910nm	-	910	nm
			660nm	-	660	nm
Half angle	△θ	I _F =20mA	-	±65	-	deg.

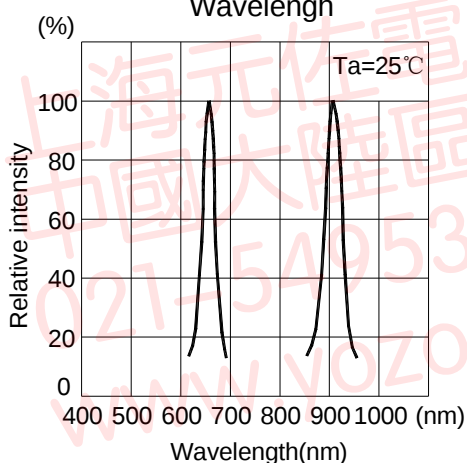
Power dissipation Vs.
Ambient temperature



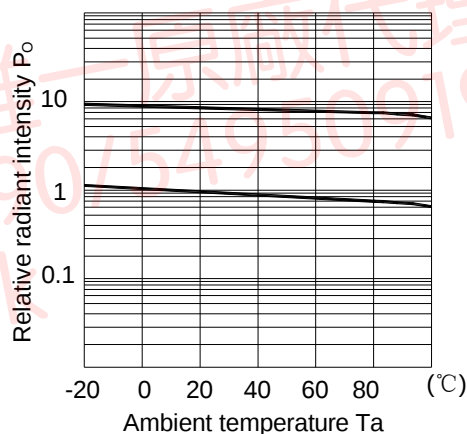
Radiant intensity Vs.
Forward current



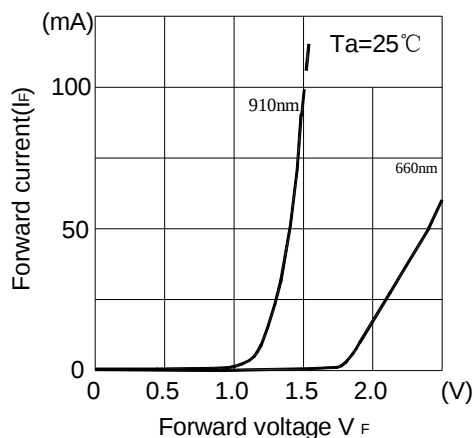
Relative sensitivity Vs.
Wavelength



Relative radiant intensity Vs.
Ambient temperature



Forward current Vs.
Forward voltage



Radiant Pattern

